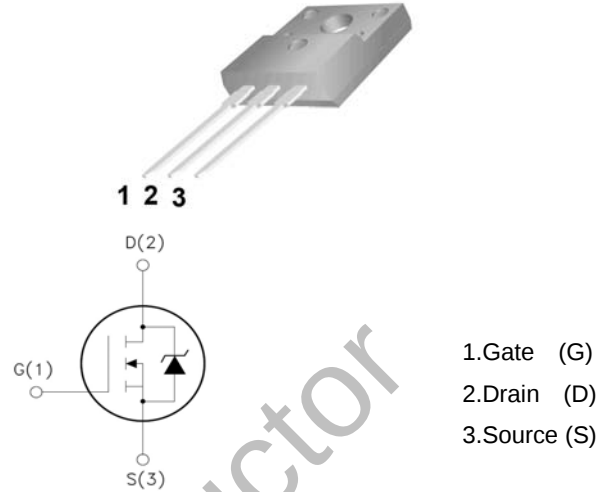


FQPF15N65SE

Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 48.5nC (Typ.).
- ☐ VDSS=650V, ID=15A
- ☐ RDS(on) : 0.52 Ω (Max) @VG=10V
- ☐ 100% Avalanche Tested

TO-220F



Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain-Source Voltage		650	V
I _D	Drain Current	T _C =25°C	15	A
		T _C =100°C	9.5	
V _{GSS}	Gate - Source voltage		±30	V
E _{AS}	Single Pulse Avalanche Energy (note1)		920	mJ
I _{AR}	Avalanche Current (note2)		15	A
P _D	Power Dissipation (Tc=25°C)		60	W
T _j	Junction Temperature(Max)		150	°C
T _{stg}	Storage Temperature		-55~+150	
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction to Case	-	2.08	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	-	62.5	

Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0	650	-	-	V
ΔBVDSS/ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA ,Reference to 25°C	-	0.71	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V, V _{GS} =0V	-	-	10	μA
		V _{DS} =480V, T _c =125°C			100	
I _{GSSF}	Gate-body leakage Current, Forward	V _{GS} =+30V, V _{DS} =0V	-	-	100	nA
I _{GSSR}	Gate-body leakage Current, Reverse	V _{GS} =-30V, V _{DS} =0V	-	-	-100	
On Characteristics						
V _{GS(TH)}	Date Threshold Voltage	I _D =250μA,V _{DS} =V _{GS}	2	-	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	I _D =7.5A,V _{GS} =10V	-	0.45	0.52	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	V _{DS} =25V, V _{GS} =0, f=1.0MHz	-	2450	-	pF
Coss	Output Capacitance		-	295	-	
Crss	Reverse Transfer Capacitance		-	23.6	-	
Switching Characteristics						
Td(on)	Turn-On Delay Time	V _{DD} =325V, I _D =15A R _G =21.7Ω (Note 3,4)	-	65	140	ns
Tr	Turn-On Rise Time		-	125	260	
Td(off)	Turn-Off Delay Time		-	105	220	
Tf	Turn-Off Rise Time		-	65	140	
Qg	Total Gate Charge	V _{DS} =480V,V _{GS} =10V, I _D =15A (Note 3,4)	-	48.5	63	nC
Qgs	Gate-Source Charge		-	14	-	
Qgd	Gate-Drain Charge		-	21	-	
Drain-Source Diode Characteristics and Maximum Ratings						
IS	Max. Diode Forward Current	-	-	-	15	A
ISM	Max. Pulsed Forward Current	-	-	-	60	
VSD	Diode Forward Voltage	I _D =15A	-	-	1.4	V
Trr	Reverse Recovery Time	IS=15A,VGS =0V diF/dt=100A/μs	496	-	-	nS
Qrr	Reverse Recovery Charge	(Note3)	5.69	-	-	μC

Notes : 1, L=8.15mH, I_{AS}=15A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C

2, Repetitive Rating : Pulse width limited by maximum junction temperature

3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

4, Essentially Independent of Operating Temperature

Typical Characteristics

Figure 1. On-Region Characteristics

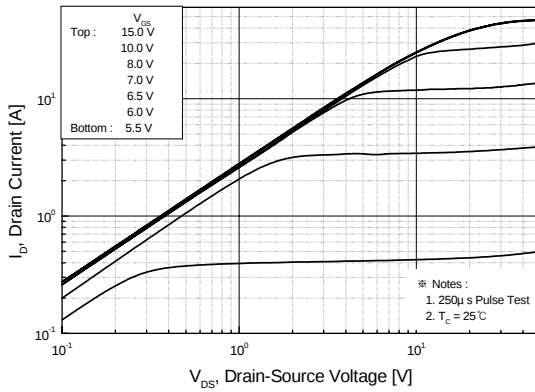


Figure 2. Transfer Characteristics

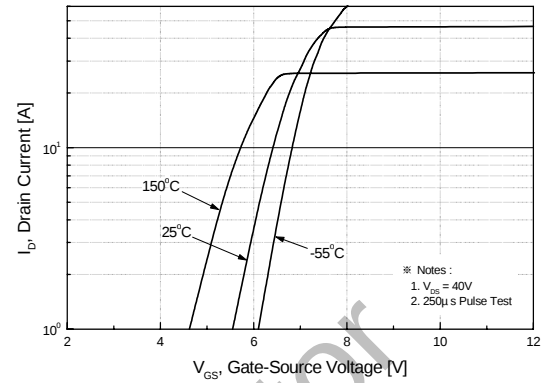


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

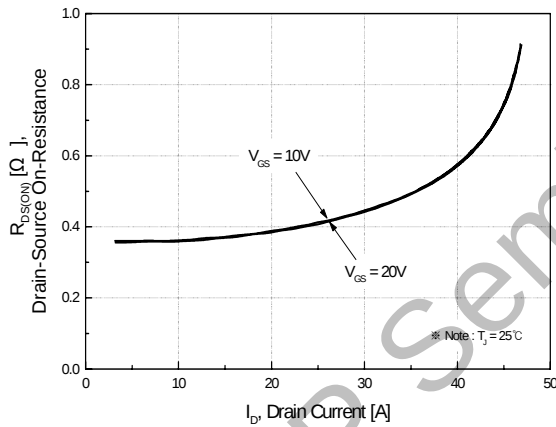


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

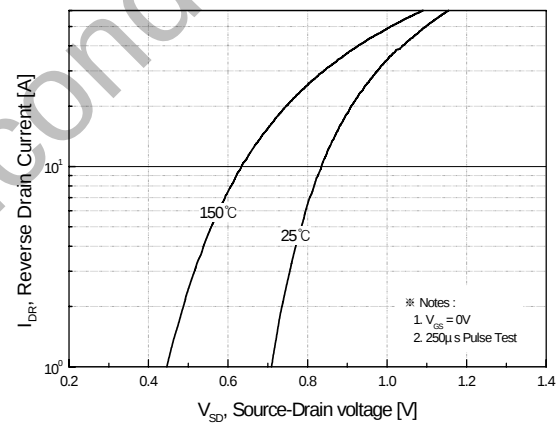


Figure 5. Capacitance Characteristics

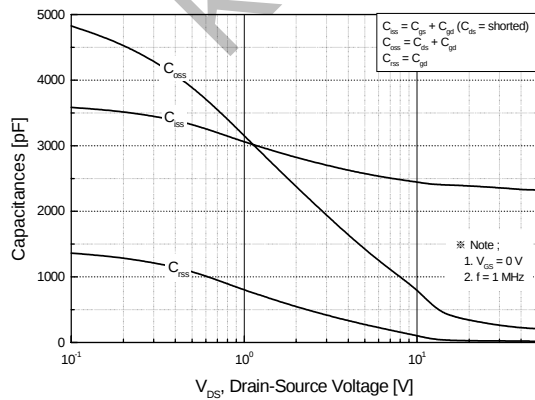
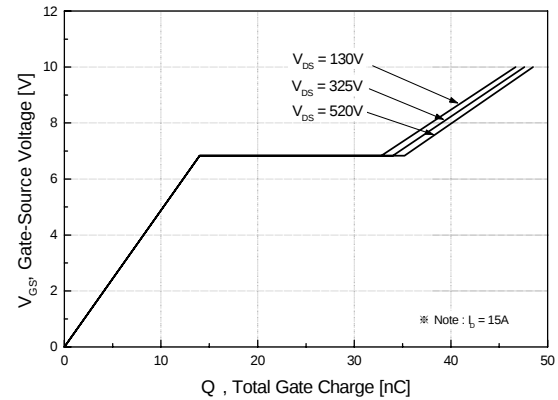


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

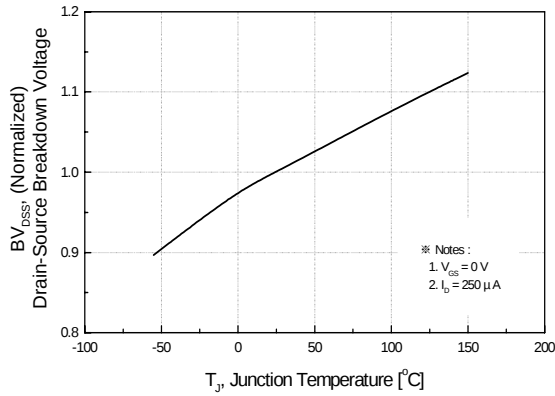


Figure 8. On-Resistance Variation vs. Temperature

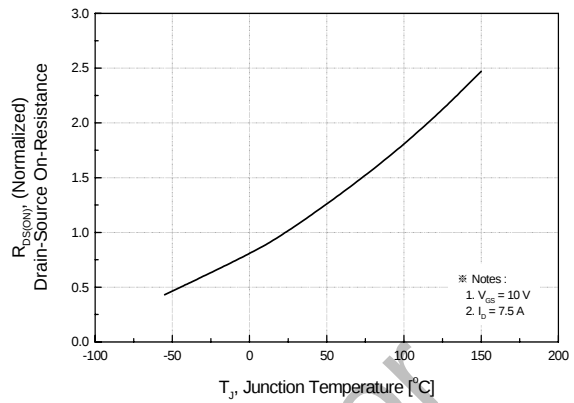


Figure 9-2. Safe Operating Area

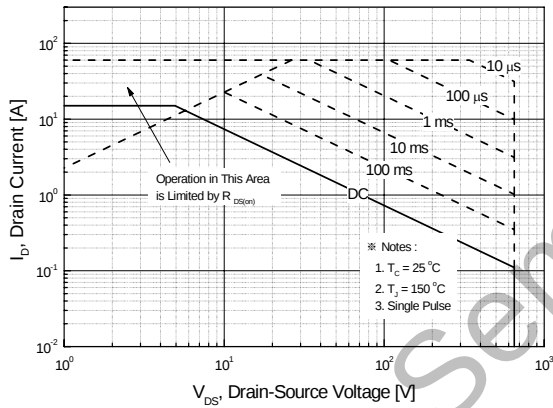


Figure 10. Maximum Drain Current vs. Case Temperature

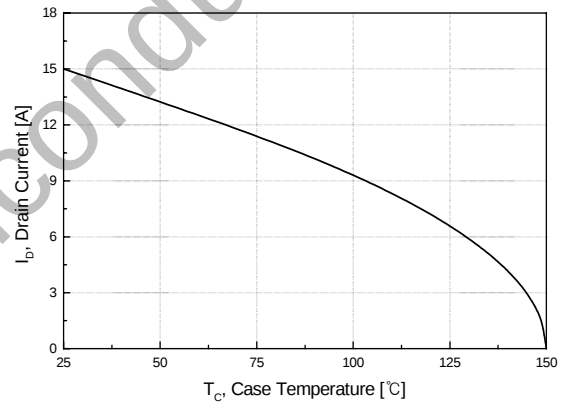
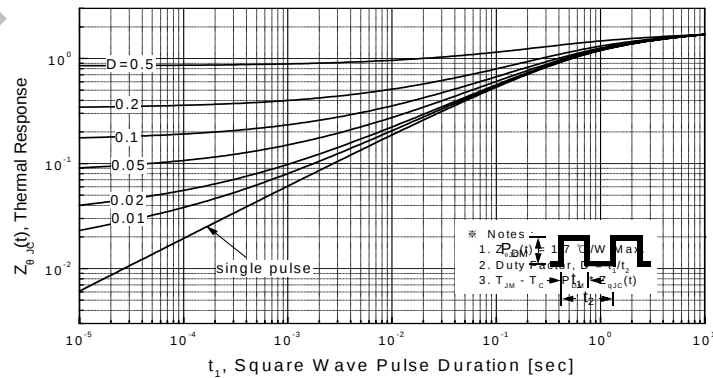
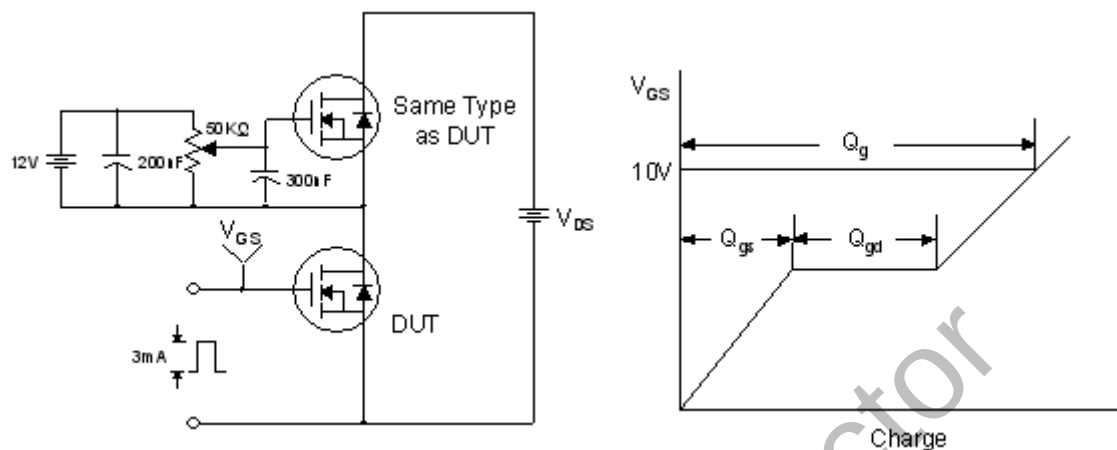


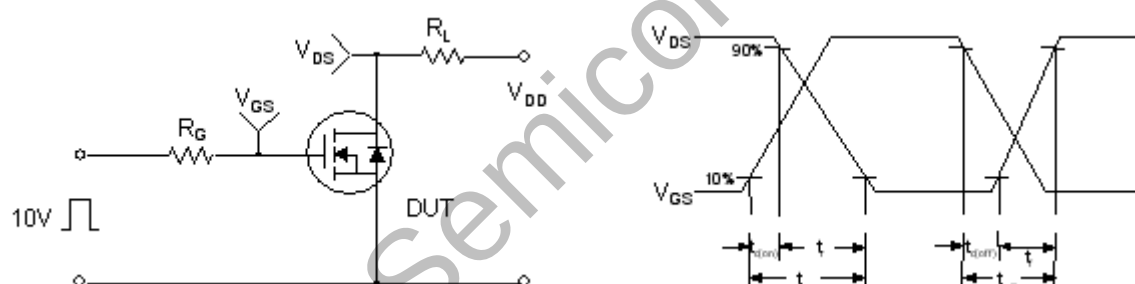
Figure 11-2. Transient Thermal Response Curve



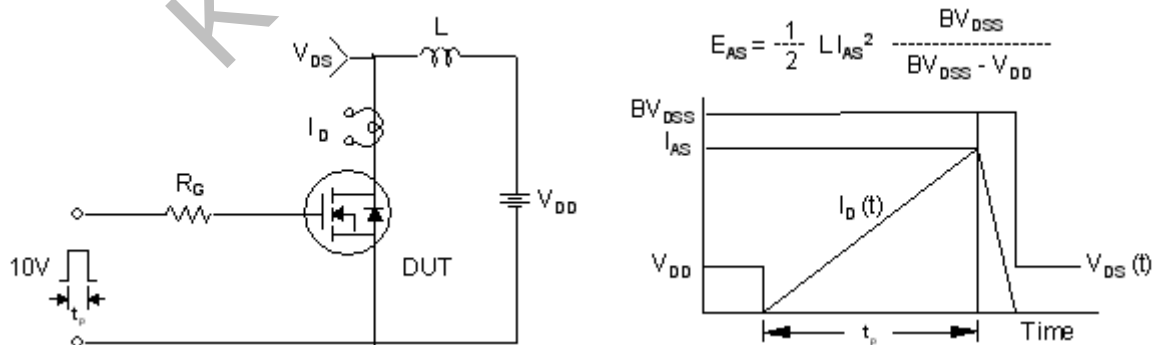
Gate Charge Test Circuit & Waveform



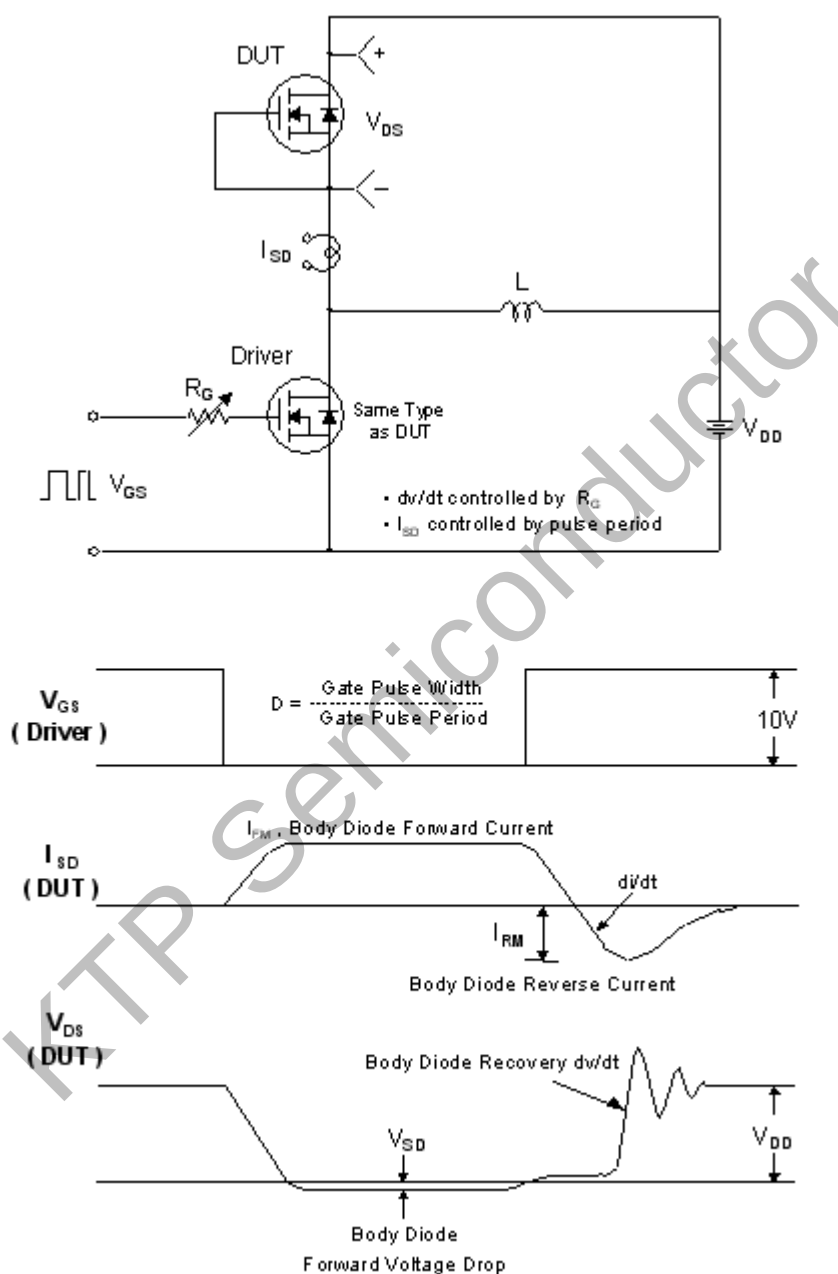
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



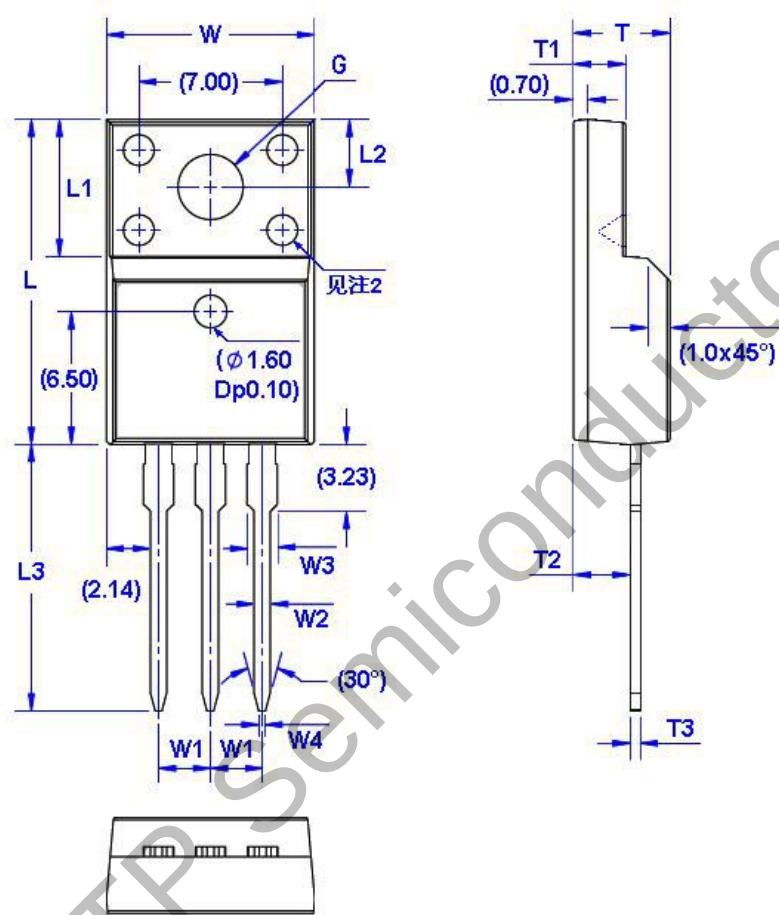
Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

TO-220F

Unit: mm



Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.96	10.36	W4	0.25	0.45	L3	12.78	13.18	T3	0.45	0.60
W1	2.54 (TYP)		L	15.67	16.07	T	4.50	4.90	G(Φ)	3.08	3.28
W2	0.70	0.90	L1	6.48	6.88	T1	2.34	2.74			
W3	1.24	1.47	L2	3.20	3.40	T2	2.56	2.96			